

54F/74F827 • 74F828 10-Bit Buffers/Line Drivers

General Description

The 'F827 and 'F828 10-bit bus buffers provide high performance bus interface buffering for wide data/address paths or buses carrying parity. The 10-bit buffers have NOR output enables for maximum control flexibility.

The 'F827 and 'F828 are functionally- and pin-compatible to AMD's Am29827 and Am29828. The 'F828 is an inverting version of the 'F827.

Features

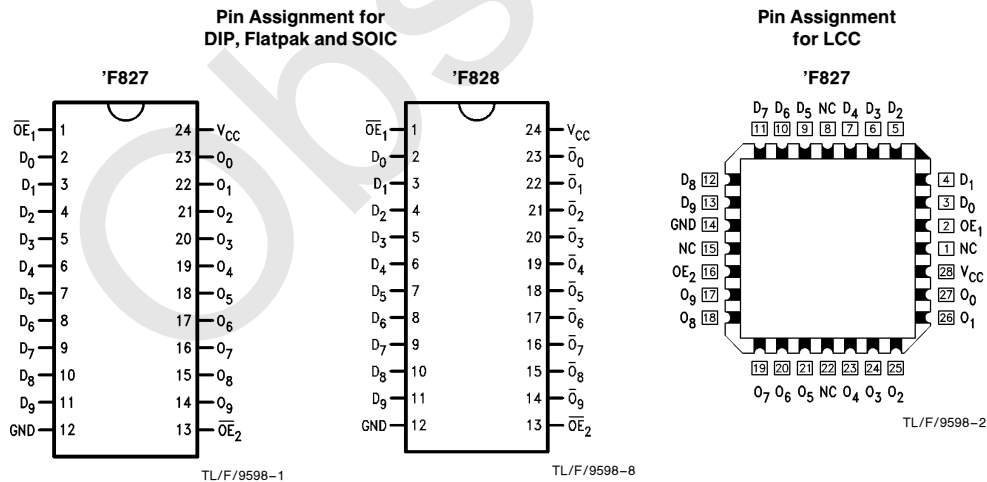
- TRI-STATE® output
- 'F828 is inverting
- Direct replacement for AMD's Am29827 and Am29828

Commercial	Military	Package Number	Package Description
74F827SPC		N24C	24-Lead (0.300" Wide) Molded Dual-In-Line
	54F827SDM (Note 2)	J24F	24-Lead (0.300" Wide) Ceramic Dual-In-Line
74F827SC (Note 1)		M24B	24-Lead (0.300" Wide) Molded Small Outline, JEDEC
	54F827FM (Note 2)	W24C	24-Lead Cerpack
	54F827LM (Note 2)	E28A	24-Lead Ceramic Leadless Chip Carrier, Type C
74F828SPC		N24C	24-Lead (0.300" Wide) Molded Dual-In-Line
74F828SC (Note 1)		M24B	24-Lead (0.300" Wide) Molded Small Outline, JEDEC

Note 1: Devices also available in 13" reel. Use suffix = SCX.

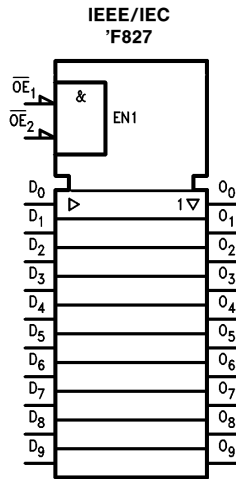
Note 2: Military grade device with environmental and burn-in processing. Use suffix = SDM QB, FM QB and LM QB.

Connection Diagrams

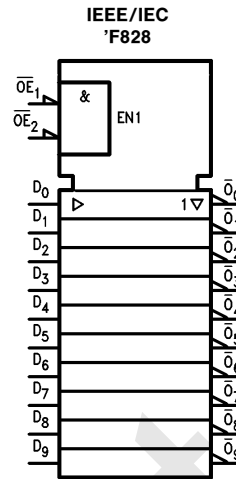


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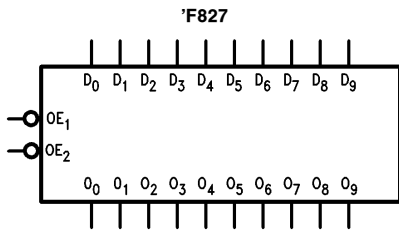
Logic Symbols



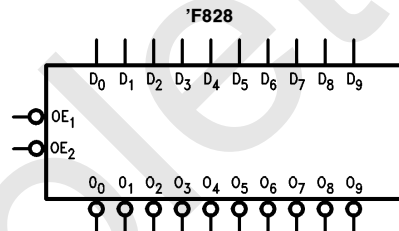
TL/F/9598-6



TL/F/9598-7



TL/F/9598-3



TL/F/9598-10

Unit Loading/Fan Out

Pin Names	Description	54F/74F	
		U.L. HIGH/LOW	Input I_{IH}/I_{IL} Output I_{OH}/I_{OL}
$\overline{OE}_1, \overline{OE}_2$	Output Enable Input	1.0/1.0	20 μA / -0.6 mA
D_0-D_7	Data Inputs	1.0/1.0	20 μA / -0.6 mA
O_0-O_7	Data Outputs, TRI-STATE	600/106.6 (80)	-12 mA/64 mA (48 mA)

Functional Description

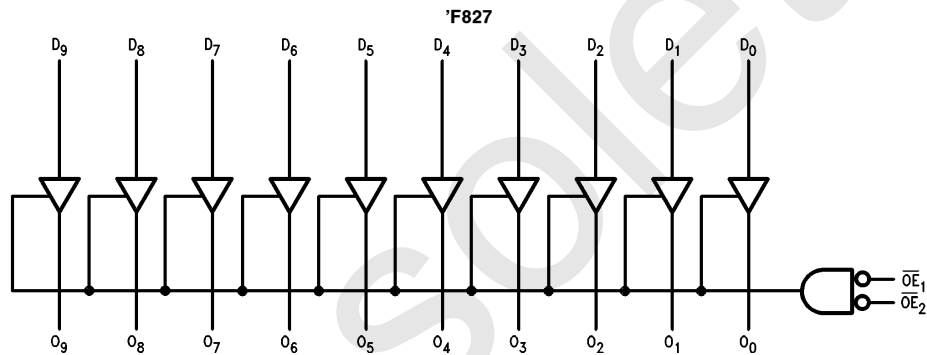
The 'F827 and 'F828 are line drivers designed to be employed as memory address drivers, clock drivers and bus-oriented transmitters/receivers which provide improved PC board density. The devices have TRI-STATE outputs controlled by the Output Enable (\overline{OE}) pins. The outputs can sink 64 mA (48 mA mil) and source 15 mA. Input clamp diodes limit high-speed termination effects.

Function Table

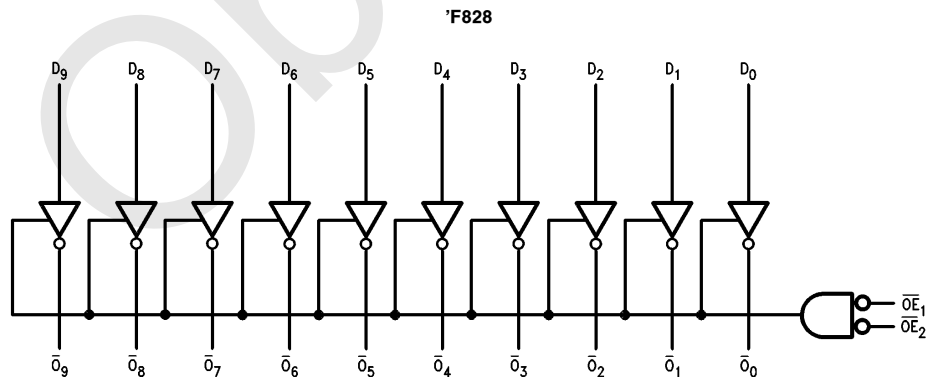
\overline{OE}	D_n	Outputs		Function
		O_n		
		'F827	'F828	
L	H	H	L	Transparent
L	L	L	H	Transparent
H	X	Z	Z	High Z

H = HIGH Voltage level
L = LOW Voltage Level
Z = High Impedance
X = Immaterial

Logic Diagrams



Please note that this diagram is provided only for the understanding of logic operations and should not be used to estimate propagation delays.



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Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Storage Temperature	-65°C to +150°C
Ambient Temperature under Bias	-55°C to +125°C
Junction Temperature under Bias	-55°C to +175°C
Plastic	-55°C to +150°C

V_{CC} Pin Potential to Ground Pin -0.5V to +7.0V

Input Voltage (Note 2) -0.5V to +7.0V

Input Current (Note 2) -30 mA to +5.0 mA

Voltage Applied to Output in HIGH State (with V_{CC} = 0V)

Standard Output	-0.5V to V _{CC}
TRI-STATE Output	-0.5V to +5.5V

Current Applied to Output in LOW State (Max) twice the rated I_{OL} (mA)

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

Recommended Operating Conditions

Free Air Ambient Temperature	
Military	-55°C to +125°C
Commercial	0°C to +70°C
Supply Voltage	
Military	+4.5V to +5.5V
Commercial	+4.5V to +5.5V

DC Electrical Characteristics

Symbol	Parameter	54F/74F			Units	V _{CC}	Conditions
		Min	Typ	Max			
V _{IH}	Input HIGH Voltage	2.0			V		Recognized as a HIGH Signal
V _{IL}	Input LOW Voltage			0.8	V		Recognized as a LOW Signal
V _{CD}	Input Clamp Diode Voltage			-1.2	V	Min	I _{IN} = -18 mA
V _{OH}	Output HIGH Voltage	54F 10% V _{CC} 54F 10% V _{CC} 74F 10% V _{CC} 74F 10% V _{CC} 74F 5% V _{CC}	2.4 2.0 2.4 2.0 2.7		V	Min	I _{OH} = -3 mA I _{OH} = -12 mA I _{OH} = -3 mA I _{OH} = -15 mA I _{OH} = -3 mA
V _{OL}	Output LOW Voltage	54F 10% V _{CC} 74F 10% V _{CC}		0.55 0.55	V	Min	I _{OL} = 48 mA I _{OL} = 64 mA
I _{IH}	Input HIGH Current	54F 74F		20.0 5.0	μA	Max	V _{IN} = 2.7V
I _{BVI}	Input HIGH Current Breakdown Test	54F 74F		100 7.0	μA	Max	V _{IN} = 7.0V
I _{CEX}	Output HIGH Leakage Current	54F 74F		250 50	μA	Max	V _{OUT} = V _{CC}
V _{ID}	Input Leakage Test	74F	4.75		V	0.0	I _{ID} = 1.9 μA All Other Pins Grounded
I _{OD}	Output Leakage Circuit Current	74F		3.75	μA	0.0	V _{IOD} = 150 mV All Other Pins Grounded
I _{IL}	Input LOW Current			-0.6	mA	Max	V _{IN} = 0.5V
I _{OZH}	Output Leakage Current			50	μA	Max	V _{OUT} = 2.7V
I _{OZL}	Output Leakage Current			-50	μA	Max	V _{OUT} = 0.5V
I _{OS}	Output Short-Circuit Current			-100	mA	Max	V _{OUT} = 0V

DC Electrical Characteristics (Continued)

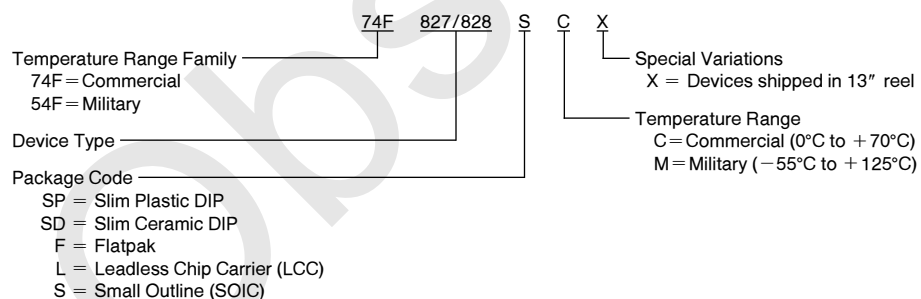
Symbol	Parameter	54F/74F			Units	V _{CC}	Conditions
		Min	Typ	Max			
I _{ZZ}	Bus Drainage Test			500	μA	0.0V	V _{OUT} = 5.25V
I _{CCH}	Power Supply Current ('F827)		30	45	mA	Max	V _O = HIGH
I _{CCL}	Power Supply Current ('F827)		60	90	mA	Max	V _O = LOW
I _{CCZ}	Power Supply Current ('F827)		40	60	mA	Max	V _O = HIGH Z
I _{CCH}	Power Supply Current ('F828)		14	20	mA	Max	V _O = HIGH
I _{CCL}	Power Supply Current ('F828)		56	85	mA	Max	V _O = LOW
I _{CCZ}	Power Supply Current ('F828)		35	50	mA	Max	V _O = HIGH Z

AC Electrical Characteristics

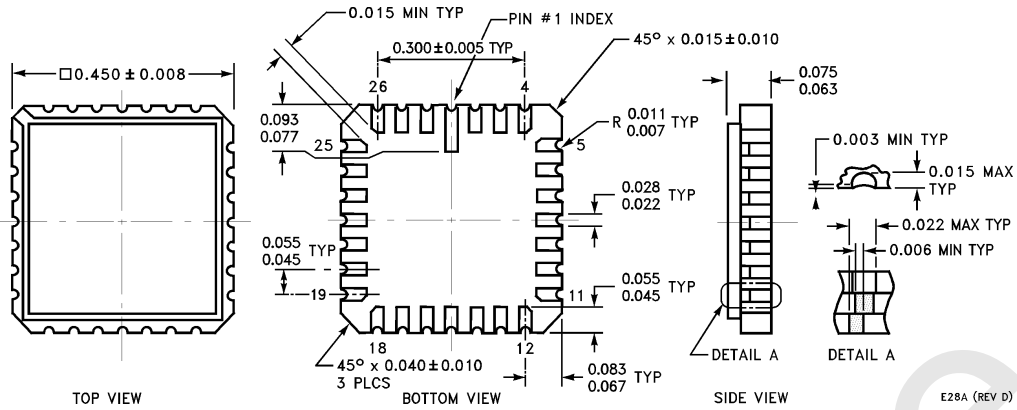
Symbol	Parameter	74F			54F		74F		Units
		T _A = +25°C V _{CC} = +5.0V C _L = 50 pF			T _A , V _{CC} = Mil C _L = 50 pF		T _A , V _{CC} = Com C _L = 50 pF		
		Min	Typ	Max	Min	Max	Min	Max	
t _{PLH} t _{PHL}	Propagation Delay Data to Output ('F827)	1.0 1.5	3.0 3.3	5.5 5.5	1.0 1.5	7.5 7.0	1.0 1.5	6.5 6.0	ns
t _{PLH} t _{PHL}	Propagation Delay Data to Output ('F828)	1.0 1.0	3.0 2.0	5.0 4.0			1.0 1.0	5.5 4.0	ns
t _{PZH} t _{PZL}	Output Enable Time \overline{OE} to O _n	3.0 3.5	5.7 6.8	9.0 11.5	2.5 3.0	10.0 12.5	2.5 3.0	9.5 12.0	ns
t _{PHZ} t _{PLZ}	Output Disable Time \overline{OE} to O _n	1.5 1.0	3.3 3.5	8.0 8.0	1.5 1.0	9.0 9.0	1.5 1.0	8.5 8.5	ns

Ordering Information

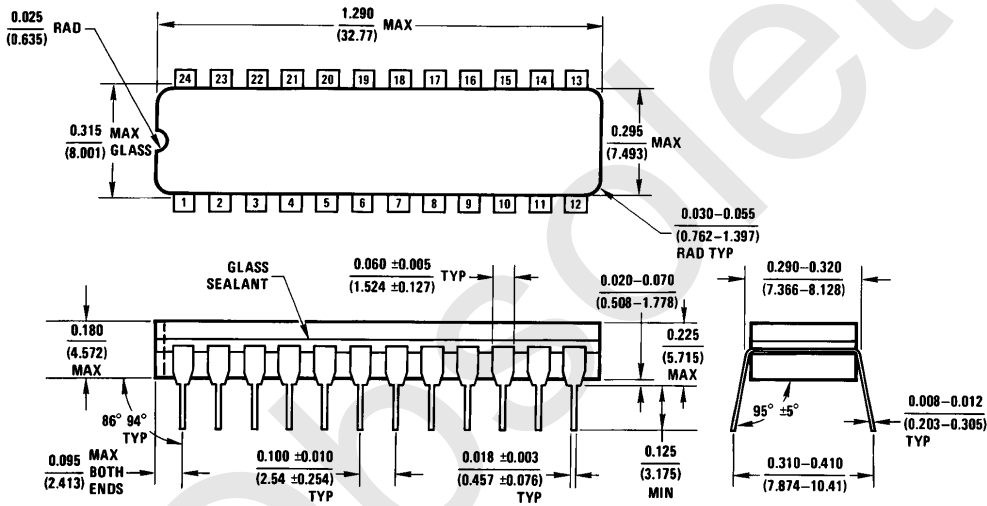
The device number is used to form part of a simplified purchasing code where the package type and temperature range are defined as follows:



Physical Dimensions inches (millimeters)

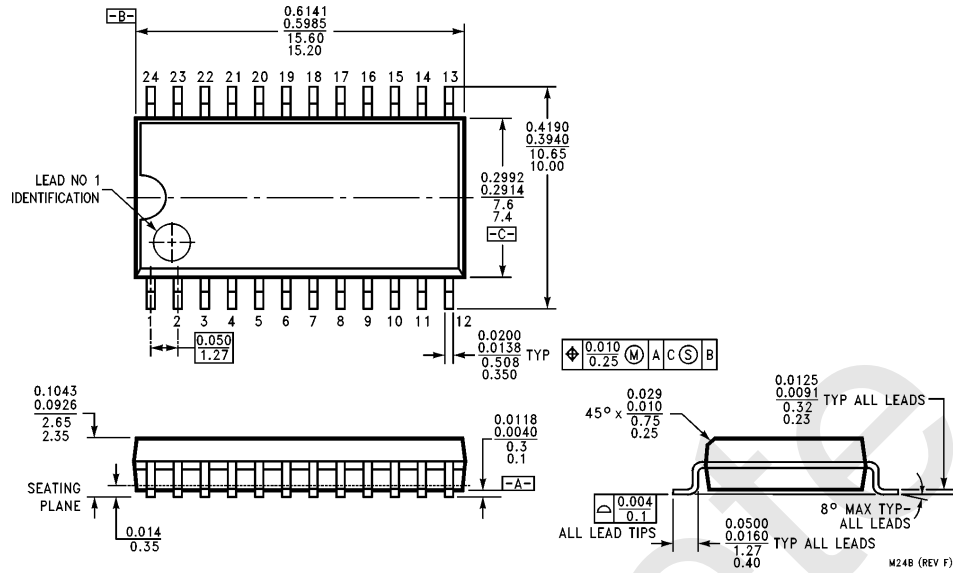


28-Lead Ceramic Leadless Chip Carrier (L)
NS Package Number E28A

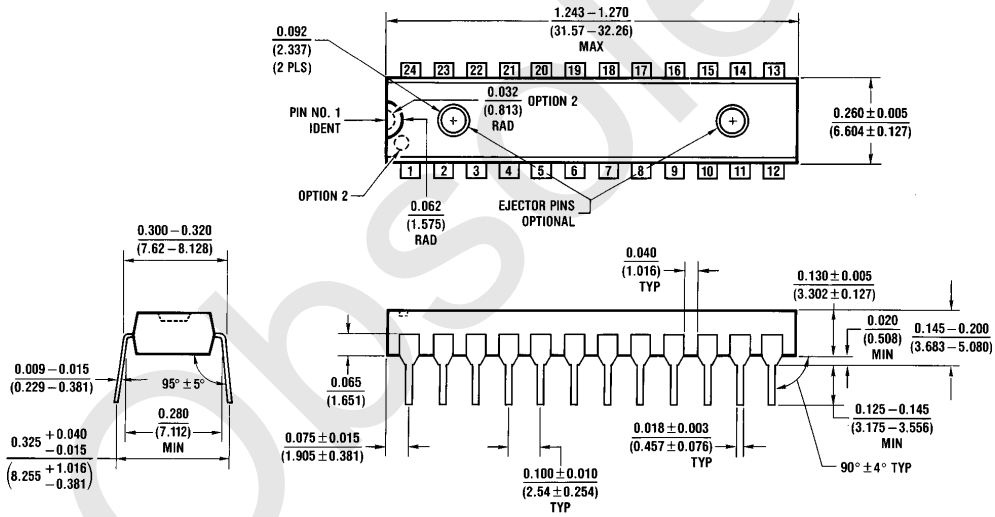


24-Lead (0.300" Wide) Ceramic Dual-In-Line Package (SD)
NS Package Number J24F

Physical Dimensions inches (millimeters) (Continued)

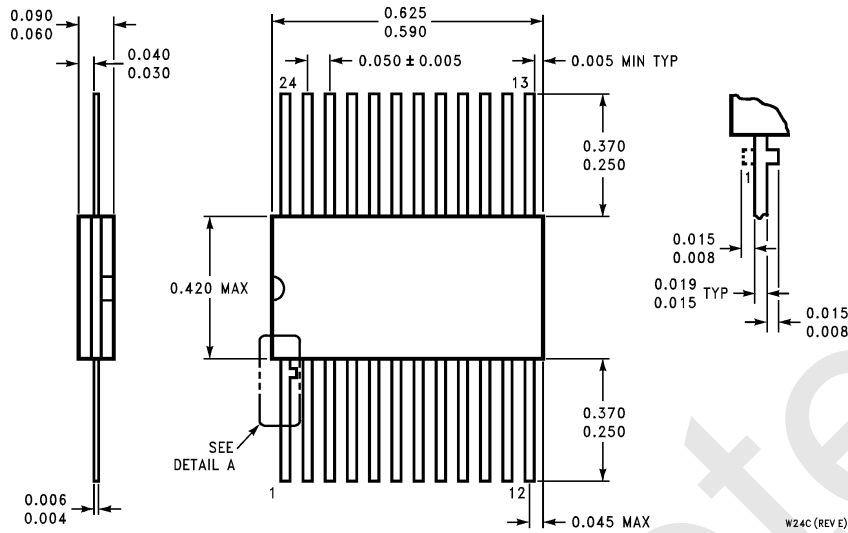


**24-Lead Small Outline Integrated Circuit (S)
NS Package Number M24B**



**24-Lead Plastic Slim (0.300" Wide) Dual-In-Line Package (SP)
NS Package Number N24C**

Physical Dimensions inches (millimeters) (Continued)



**24-Lead Ceramic Flatpak (F)
NS Package Number W24C**

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